

(Previously Presented) 1. An amplified laser source for amplifying a laser projection comprising:

a diode laser source modulated by a pulse generator applying an alternate high and low voltages higher and lower than a threshold voltages projecting a modulated optical signal;

a first erbium doped fiber (EDF) for amplifying said modulated optical signal;

a set of Bragg gratings for receiving said modulated optical signal from said first EDF for reflecting a grating-specific pulse-distortion-reduced optical signal and a circulator for transmitting said grating-specific pulse-distortion-reduced optical signal to a second erbium doped fiber for further amplification.

(Previously Presented) 2. The amplified laser source of claim 1 further comprising:

an Electro-Absorption (EA) modulator synchronized with said pulse generator for increasing an extinction ratio of said optical signals.

(Previously Presented) 3. The amplified laser source of claim 2 further comprising:

said second erbium doped fiber (EDF) receiving and amplifying said optical signal from said Electro-Absorption (EA) modulator.

(Original) 4. The amplified laser source of claim 3 wherein:

said second erbium doped fiber (EDF) having a large mode area.

(Currently Amended) 5. The amplified laser source of claim 3 wherein:

said second erbium doped fiber (EDF) having a length of several meters and a diameter approximately thirty-five in a range ~~substantially between ten to one-hundred~~ micrometers.

(Original) 6. The amplified laser source of claim 2 wherein:

said EA modulator is a semiconductor Electro-Absorption (EA) modulator.

(Currently Amended) 7. An amplified laser source for amplifying a laser projection comprising:

a diode laser source modulated by a pulse generator applying an alternate high and low voltages higher and lower than a threshold voltages projecting a modulated optical signal;

a first erbium doped fiber (EDF) for amplifying said modulated optical signal;

a set of Bragg gratings for receiving said modulated optical signal from said first EDF for reflecting a grating-specific pulse-distortion-reduced optical signal;

a circulator for transmitting said grating-specific pulse-distortion-reduced optical signal to an EA modulator synchronized with said pulse generator for increasing an extinction ratio of said optical signals; and

a second erbium doped fiber (EDF) for receiving and amplifying said optical signal from said EA modulator wherein said second erbium doped fiber (EDF) having a length of several meters and a diameter approximately thirty-five in a range ~~substantially between ten to one-hundred~~ micrometers.

(Previously Presented) 8. An amplified laser source for amplifying a laser projection comprising:

a first laser gain medium for amplifying said laser projection for projecting to a set of Bragg gratings for reflecting a grating-specific pulse-distortion-reduced optical signal and a circulator for transmitting said grating-specific pulse-distortion-reduced optical signal to a second laser gain medium for further amplification; and

an EA modulator synchronized with said pulse generator for increasing an extinction ratio of said optical signals.

(Original) 9. The amplified laser source of claim 8 further comprising:

a diode laser source modulated by a pulse generator applying an alternate high and low voltages higher and lower than a threshold voltages projecting a modulated optical signal to said Bragg gratings.

(Previously Presented) 10. The amplified laser source of claim 9 wherein:

said first laser gain medium comprising a first erbium doped fiber (EDF) for amplifying said modulated optical signal.

(Canceled) 11. The amplified laser source of claim 8 further comprising:

an EA modulator synchronized with said pulse generator for increasing an extinction ratio of said optical signals.

(Previously Presented) 12. The amplified laser source of claim 8 wherein:

said second laser gain medium comprising a second erbium doped fiber (EDF) for receiving and amplifying said optical signal from said EA modulator.

(Original) 13. The amplified laser source of claim 12 wherein:

said second erbium doped fiber (EDF) having a large mode area.

(Currently Amended) 14. The amplified laser source of claim 12 wherein:

said second erbium doped fiber (EDF) having a length of several meters and a diameter **approximately thirty-five in a range**
substantially between ten to one hundred micrometers.

(Previously Presented) 15. The amplified laser source of claim 8 wherein:

said EA modulator is a semiconductor EA modulator.

(Withdrawn) 16. A method for configuring an amplified laser source for amplifying a laser projection comprising:

employing a set of Bragg gratings for reflecting a grating-specific pulse-distortion-reduced optical signal.

(Withdrawn) 17. The method of claim 16 further comprising:

modulating a diode laser source by a pulse generator applying an alternate high and low voltages higher and lower than a threshold voltages for projecting a modulated optical signal to said Bragg gratings.

(Withdrawn) 18. The method of claim 17 further comprising:

amplifying an optical signal from said diode laser by a first erbium doped fiber (EDF).

(Withdrawn) 19. The method of claim 17 further comprising:

transmitting said optical signals via an EA modulator synchronized with said pulse generator.

(Withdrawn) 20. The method of claim 18 further comprising:

implementing a second erbium doped fiber (EDF) for receiving and amplifying said optical signal from said EA modulator.

(Withdrawn) 21. The method of claim 20 wherein:

said step implementing a second EDF is a step of implementing said second erbium doped fiber (EDF) having a large mode area.

(Withdrawn) 22. The method of claim 20 wherein:

said step implementing a second EDF is a step of implementing said second erbium doped fiber (EDF) having a length of several meters and a diameter greater than or equal to thirty-five micrometers.

(Withdrawn) 23. The method of claim 19 wherein:

transmitting said optical signals via an EA modulator is a step of transmitting said optical signals via a semiconductor EA modulator.